

Preface for Special Issue: Advancements in Semiconductor Lasers

Hong, Yanhua; Masoller, Cristina; Lee, Min Wong

Photonics

DOI:

[10.3390/photonics10080944](https://doi.org/10.3390/photonics10080944)

Published: 18/08/2023

Peer reviewed version

[Cyswllt i'r cyhoeddiad / Link to publication](#)

Dyfyniad o'r fersiwn a gyhoeddwyd / Citation for published version (APA):

Hong, Y., Masoller, C., & Lee, M. W. (2023). Preface for Special Issue: Advancements in Semiconductor Lasers. *Photonics*, 10(8), Article 944. <https://doi.org/10.3390/photonics10080944>

Hawliau Cyffredinol / General rights

Copyright and moral rights for the publications made accessible in the public portal are retained by the authors and/or other copyright owners and it is a condition of accessing publications that users recognise and abide by the legal requirements associated with these rights.

- Users may download and print one copy of any publication from the public portal for the purpose of private study or research.
- You may not further distribute the material or use it for any profit-making activity or commercial gain
- You may freely distribute the URL identifying the publication in the public portal ?

Take down policy

If you believe that this document breaches copyright please contact us providing details, and we will remove access to the work immediately and investigate your claim.

Preface for Special Issue: Advancements in Semiconductor Lasers

Yanhua Hong ^{1,*}, Cristina Masoller ² and Min Won Lee ³

¹ School of Computer Science and Engineer, Bangor University, Bangor LL57 1UT, UK

² Physics Department, Universitat Politècnica de Catalunya, Rambla St. Nebridi 22, 08222 Terrassa, Spain; cristina.masoller@upc.edu

³ Laboratoire de Physique des Lasers (UMR CNRS 7538), Université Sorbonne Paris Nord 93430 Villetaneuse, France; min.lee@univ-paris13.fr

* Correspondence: y.hong@bangor.ac.uk

We are delighted to present this special issue of "Advancement of Semiconductor Lasers," which features a remarkable collection of 14 papers that explore the diverse and cutting-edge aspects of semiconductor lasers. This collection brings together the latest research and innovations in the field, covering topics ranging from new techniques for understanding laser dynamics to devices design and fabrication, investigation of laser dynamics and their applications, and the characterization of compounded semiconductor materials.

Semiconductor lasers have revolutionized various industries, enabling critical advancements in telecommunications, data communication, sensing, and imaging applications. With a continuous pursuit of higher performance and novel functionalities, the field of semiconductor lasers has witnessed remarkable progress over the years. This special issue showcases some of the most exciting developments and discoveries from leading researchers around the world.

The first section of this issue presents advancement in understanding the underlying determinism of semiconductor lasers, and a new method to distinguish chaotic regimes in a semiconductor laser with feedback. Lenstra et al. offer physical insight into the noise-triggered spiking mechanism in a two-section semiconductor laser under excitable and noisy conditions, with potential implications for studying stochastic spiking in biological neurons [1]. Nguyen et al. develop Temporal And Reversible Dynamical Symmetry (TARDYS) quantifiers, providing a powerful tool for characterizing chaotic regimes in other complex dynamical systems [2].

The second section of this issue presents four papers dedicated to the exploration of new types of semiconductor lasers and devices. Among these, Panajovtsov et al. introduce a groundbreaking spin-VCSEL, which embeds a nematic liquid crystal in a second cavity, achieving an astonishing small signal modulation response of several hundreds of GHz [3]. This advancement represents a significant breakthrough, outperforming conventional VCSELs by more than 10 times. Sun et al. focus on the design and fabrication of a trench mode-modulation based edge-emitting laser operating at 650nm [4]. This device not only demonstrates superior beam quality but also maintains high power output. Moreover, Liu et al. reports the successful fabrication of a 792nm semiconductor laser with an impressive output power of 232 W and an electro-optic conversion efficiency of 48.6% [5]. Such high-power lasers hold great promise for various industrial and scientific applications. In another significant contribution, a monolithically integrated multi-section

Citation: Lastname, F.; Lastname, F.; Lastname, F. Title. *Photonics* **2022**, *9*, x. <https://doi.org/10.3390/xxxxx>

Received: date

Accepted: date

Published: date

Publisher's Note: MDPI stays neutral with regard to jurisdictional claims in published maps and institutional affiliations.



Copyright: © 2022 by the authors. Submitted for possible open access publication under the terms and conditions of the Creative Commons Attribution (CC BY) license (<https://creativecommons.org/licenses/by/4.0/>).

semiconductor laser is introduced, showcasing enhanced security with 248 key spaces and a data rate of 2.5 Gb/s [6].

Further expanding on the study of nonlinear dynamics of semiconductor lasers and their applications, Zhao et al. experimentally investigates the nonlinear dynamics of an interband cascade laser under variable-aperture optical feedback, revealing various dynamical states [7]. Additionally, the mode configuration of an excited-state quantum dot laser (ES-QDL) under concave mirror optical feedback, demonstrating selective excitation of longitudinal modes is explored [8]. Bian et al. proposes a simple method using mutually coupled free-running VCSELs to generate broadband polarization chaos [9], while the locking map of a semiconductor laser under the injection of a frequency comb is studied [10]. Moreover, a new technique using feedback-delay signatures of a modulated semiconductor laser for fiber fault detection is introduced to enhance detection sensitivity [11]. The effect of VCSEL temperature on the quality of random number generation is explored [12], and the potential of generating high-quality photonic microwave signals in solitary QD spin-VCSELs with optical feedback is demonstrated [13].

Finally, Mikhailov et al. delve into the characterization of compound semiconductor materials [14], specifically the interband electron transition energy in multiple Hg_{1-x}Cd_xTe/Hg_{1-y}Cd_yTe quantum wells (MQWs) at room temperature.

The fascinating array of topics covered in this special issue highlights the vibrancy and dynamism of the field of semiconductor lasers. We would like to thank all the authors who submitted their exceptional work to this Special Issue. Additionally, we would like to extend our appreciation to the reviewers for their outstanding efforts in evaluating the manuscripts and offering valuable feedback. We would also like to acknowledge Photonics for initiating this special Issue, especially, the managing editor Zane Lin for her preparation, editing, and managing of this Special Issue.

We hope this special issue will inspire further exploration and collaboration in the advancement of semiconductor laser technology, fostering continued progress and innovation in the years to come.

Conflicts of Interest: The authors declare no conflict of interest.

References

1. Lenstra, D.; Puts, L.; Yao, W. M. First-passage-time analysis of the pulse-timing statistics in a two-section semiconductor laser under excitable and noisy conditions. *Photonics* **2022**, *9*, 860. 74
2. Nguyen, N. V.; Pattanayak, A. K. Aragonese A. TARDYS quantifiers: extracting temporal and reversible dynamical symmetries. *Photonics* **2022**, *9*, 938. 75
3. Panajovtov, K.; Petrov, M.; Marinov, T. Liquid-crystal spin-VCSEL with electro-optically controllable birefringence. *Photonics* **2023**, *9*, 179. 76
4. Sun, X.; Liu, P.; Ma, X. G.; Zhang, X. D.; Su, J.; Chen, K.; Liu Q.; Jiang, K.; Tang, W. J.; Xia, W.; Xu, X. G. Mode-modulation structure based on 650 nm ridge waveguide edge-emitting laser. *Photonics* **2023**, *10*, 302. 77
5. Liu, P.; Sun, W. G.; Sun, X.; Zhu, Z.; Qin, H. B.; Su, J.; Liu, C. C.; Tang, W. J.; Jiang, K.; Xia, W.; Xu, X. G. High-power 792 nm fiber-coupled semiconductor laser. *Photonics* **2022**, *9*, 619. 78
6. Zhang, F. F.; Wang, Y. C.; Sun, Y. H.; Xu, J. P.; Li, P.; Wang, A. B.; Q. Y. W. Key space enhancement in chaotic secure communication utilizing monolithically integrated multi-section semiconductor lasers. *Photonics* **2023**, *10*, 213. 79
7. Zhao, M. R.; Xia, G. X.; Yang, K.; Liu, S. M.; Liu, J. Q.; Wang, Q. P.; Liu, J. L.; Wu. Z. M. Nonlinear dynamics of mid-infrared interband cascade lasers subject to variable-aperture optical feedback, *Photonics* **2022**, *9*, 410. 80
8. Zheng, Y. F.; Xia, G. X.; Lin, X. D.; Wang, Q. Q.; Wang, H. P.; Jiang, C.; Chen, H. M.; Wu. Z. M. Experimental investigation on the mode characteristics of an excited-state quantum dot laser under concave mirror optical feedback. *Photonics* **2023**, *10*, 166. 81
9. Bian, H. F.; Zhang, X. M.; Li, P.; Jia, Z. W.; Li, M.; Xu' B. J.; Shore, K. A.; Qin, Y. W.; Wang, Y. C. Sub-40 GHz broadband polarization chaos generation using mutually coupled free-running VCSELs. *Photonics* **2023**, *10*, 219. 82
10. Al-Hosiny N. M. Dynamics of the frequency shifts in semiconductor lasers under the injection of a frequency comb. *Photonics* **2022**, *9*, 886. 83
11. Shi, Z. X.; Zhao, T.; Wang, Y. C.; Wang, A. B. High-sensitivity fiber fault detection method using feedback-delay signature of a modulated semiconductor laser. *Photonics* **2022**, *9*, 454. 84
12. Rivero, I.; del Pozo, A. L.; Valle-Miñón, M.; Quirce, A.; Valle, A. Measurement of the temperature dependence of polarization switching in gain-switched VCSELs for quantum random number generation. *Photonics* **2023**, *10*, 474. 85
13. Shen, Z. Y.; Huang, Y.; Zhu, X.; Zhou, P.; Mu, P. H.; Li, N. Q. Broad tunable and high-purity photonic microwave generation based on an optically pumped QD spin-VCSEL with optical feedback. *Photonics* **2023**, *10*, 326. 86
14. Mikhailov, N. N.; Dvoretzky, S. A.; Remesnik, V. G.; Uzhakov, I. N.; Shvets, V. A.; Aleshkin, V. Y. Interband electron transitions energy in multiple HgCdTe quantum wells at room temperature. *Photonics* **2023**, *10*, 430. 87